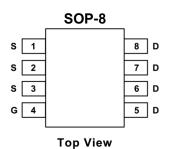
SI4435DY-T1-GE3-HX P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
VDS (V)	RDS(on) (Ω)	Qg (Typ.)	ID (A)d			
-30	0.018 at Vgs = - 10 V	1250	-9.0			
	0.024 at Vgs = - 4.5 V	13nC	-7.8			





FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g Tested

APPLICATIONS

- Load Switch
- Battery Switch

Absolute Maximum Ratings							
	Parameter	Max.	Units				
V _{DS}	Drain- Source Voltage	-30	V				
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ -10V	-8.0					
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ -10V	-6.4	Α				
I _{DM}	Pulsed Drain Current ©	-50					
P _D @T _A = 25°C	Power Dissipation	2.5	W				
P _D @T _A = 70°C	Power Dissipation	1.6	VV				
	Linear Derating Factor	0.02	W/°C				
V_{GS}	Gate-to-Source Voltage	± 20	V				
T _J , T _{STG}	Junction and Storage Temperature Range	-55 to + 150	°C				

Thermal Resistance					
	Parameter	Max.	Units		
R _θ ЈА	Maximum Junction-to-Ambient©	50	°C/W		

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Electrical Characteristics @ TJ = 25°C (unless otherwise specified)							
	Parameter	Min.	Тур.	Max.	Units	Conditions	
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-30			V	$V_{GS} = 0V, I_{D} = -250\mu A$	
$\Delta V_{(BR)DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient		-0.019		V/°C	Reference to 25°C, I_D = -1mA	
R _{DS(on)}	Static Drain-to-Source		0.015	0.020		$V_{GS} = -10V, I_{D} = -8.0A \odot$	
25(6)	On-Resistance		0.026	0.035		$V_{GS} = -4.5V, I_{D} = -5.0A \odot$	
V _{GS(th)}	Gate Threshold Voltage	-1.0			V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
gfs	Forward Transconductance		11		S	$V_{DS} = -15V, I_{D} = -8.0A$	
I _{DSS}	Drain-to-Source Leakage Current			-10		V_{DS} = -24V, V_{GS} = 0V	
1000	Brain-to-Source Leakage Current			-10	μA	$V_{DS} = -15V, V_{GS} = 0V,$	
						$T_J = 70^{\circ}C$	
I _{GSS}	Gate-to-Source Forward Leakage			-100	nA	$V_{GS} = -20V$	
000	Gate-to-Source Reverse Leakage			100	11/4	$V_{GS} = 20V$	
Q_g	Total Gate Charge		40	60		ID = -4.6A	
Qgs	Gate-to-Source Charge		7.1		nC	VDS = -15V	
Qgd	Gate-to-Drain ("Miller") Charge		8.0			Vgs = -10V ©	
td(on)	Turn-On Delay Time		16	24		VDD = -15V, VGS = -10V ©	
t _r	Rise Time		76	110	ns	ID = -1.0A	
td(off)	Turn-Off Delay Time		130	200		RG = 6.0	
t _f	Fall Time		90	140		RD = 15	
Ciss	Input Capacitance		2320			VGS = 0V	
Coss	Output Capacitance		390		pF	VDS = -15V	
Crss	everse Transfer Capacitance — 270 —			f = 1.0kHz			

Sou	rce-Drain Ratings and Ch					
	Parameter	Min.	Тур.	Max.	Units	Conditions
Is	Continuous Source Current			-2.5		MOSFET symbol
	(Body Diode)				Α	showing the
Ism	Pulsed Source Current			-50		integral reverse G
	(Body Diode) ©					p-n junction diode.
VsD	Diode Forward Voltage			-1.2	V	T _J = 25°C, I _S = -2.5A, V _{GS} = 0V ©
trr	Reverse Recovery Time		34	51	ns	$T_J = 25^{\circ}\text{C}, I_F = -2.5\text{A}$
Qrr	Reverse Recovery Charge		33	50	nC	di/dt = -100A/μs ©

Notes:

°Repetitive rating; pulse width limited by max. junction temperature.

°Pulse width ≤ 300 µs; duty cycle ≤ 2%.

© Surface mounted on FR-4 board, t ≤5sec.

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

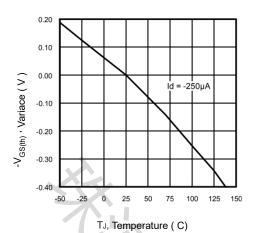
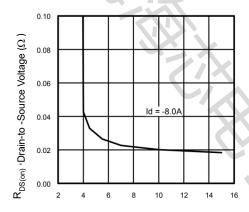


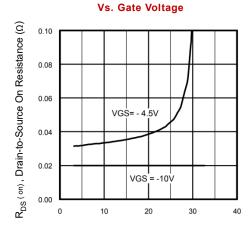
Fig 1. Typical Vgs(th) Variance





-V $_{\rm GS}$, Gate -to -Source Voltage (V)

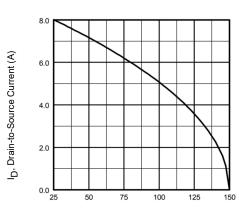
Fig 3.Typical On-Resistance



-I_D , Drain Current (A)

Fig 5. Typical On-Resistance

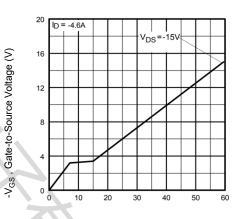
Vs. Drain Current



T_J, Case Temperature (C)

Fig 2. Maximum Drain Current

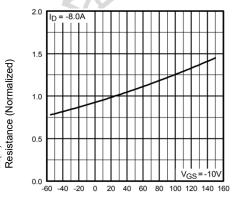




Q_G, Total Gate Charge (nC)

Fig 4. Typical Gate Charge

Vs. Gate-to-Source Voltage



T_J -Junction Temperature (°C)

Fig 6. Normalized On-Resistance

Vs. Temperature

R_{DS(on)} , Drain-to-Source On

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

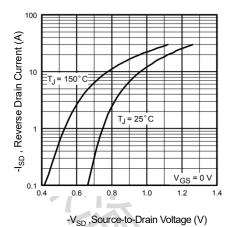
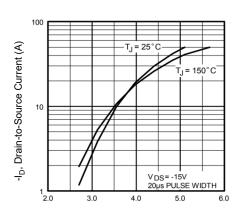
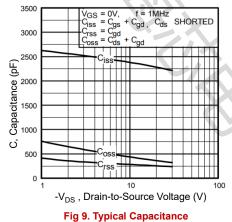


Fig 7. Typical Source-Drain Diode Forward Voltage



-V_{GS}, Gate-to-Source Voltage (V)
Fig 8. Typical Transfer Characteristics



Vs. Drain-to-Source Voltage

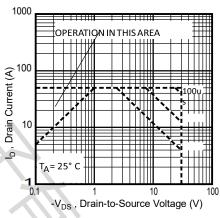
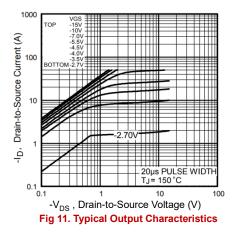


Fig 10. Maximum Safe Operating Area



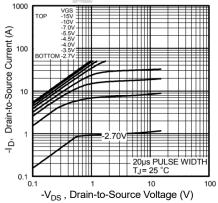


Fig 12. Typical Output Characteristics

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

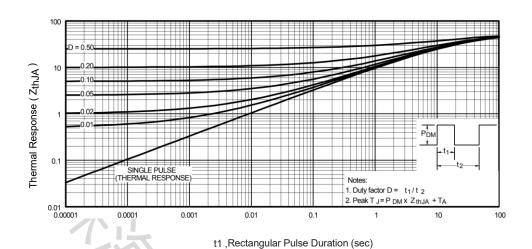
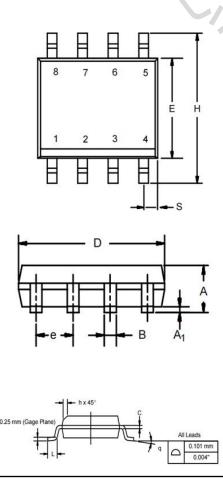


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

SOP-8 Package Outline

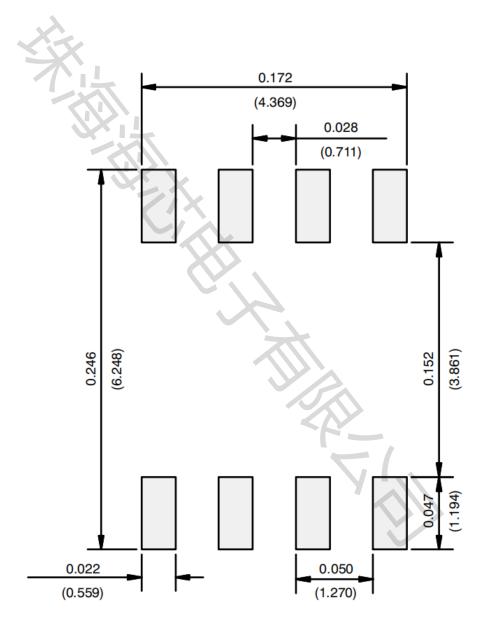
Dimensions are shown in millimeters (inches)



	MILLIM	ETERS	INCHES		
DIM	Min	Max	Min	Max	
A	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	

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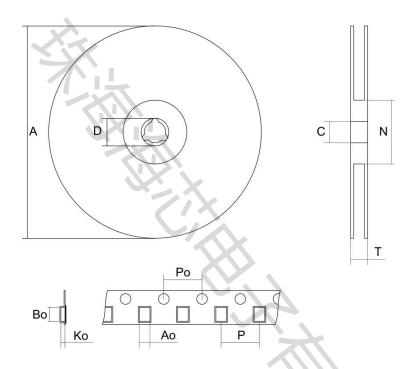
RECOMMENDED MINIMUM PADS FOR SOP-8



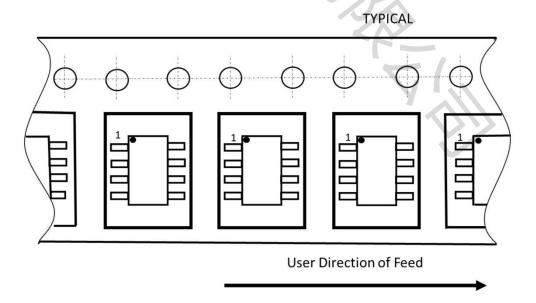
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SOP-8 packing information

SOP-8 tape and reel



Tape orientation



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